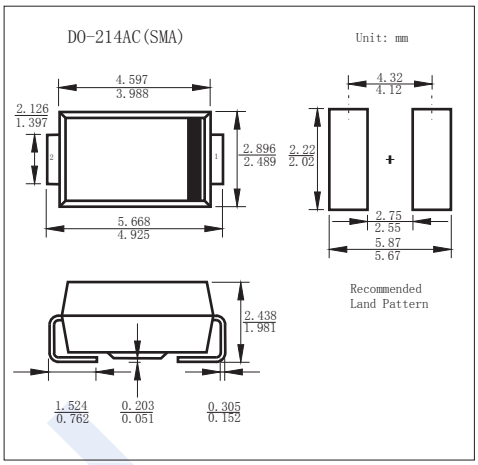
Schottky Diodes

SB170 ~ SB1100



■ Features

- Guard Ring Die Construction for Transient Protection
- Ideally Suited for Automated Assembly
- Low Power Loss, High Efficiency
- Surge Overload Rating to 30A Peak
- Lead Free Finish/RoHS Compliant
- Green Molding Compound

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	SB170	SB180	SB190	SB1100	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	70	80	90	100	V
Working Peak Reverse Voltage	V_{RWM}					
Maximum DC Blocking Voltage	V_{DC}					
RMS Reverse Voltage	$V_{R(RMS)}$	49	56	63	70	
Forward Voltage @ I_F=1A	V_F	0.79				
Forward Voltage @ I_F=1A Ta = 100℃		0.69				
Averaged Forward Current.T_T=110℃	I_{FAV}	1				A
Peak Forward Surge Current @ 8.3ms	I_{FSM}	30				
Repetitive Peak Reverse Current	I_{RRM}	1				
Maximum DC Reverse Current Ta=25℃	I_R	0.5				mA
Ta=100℃		5				
Typical Junction Capacitance @ V_R = 4V,f = 1MHz	Cj	80				pF
Typical Thermal Resistance, Junction to Terminal	$R_{\theta JT}$	25				°C/W
Junction Temperature	Tj	150				℃
Storage Temperature	Tstg	-65 to 150				

■ Marking

NO.	SB170	SB180	SB190	SB1100
Marking	B170	B180	B190	B1100

Schottky Diodes

SB170 ~ SB1100

■ Typical Characterisitics

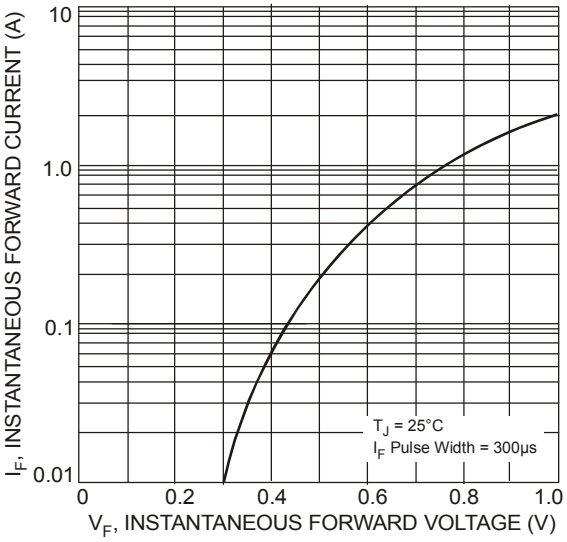


Fig. 1 Typical Forward Characteristics

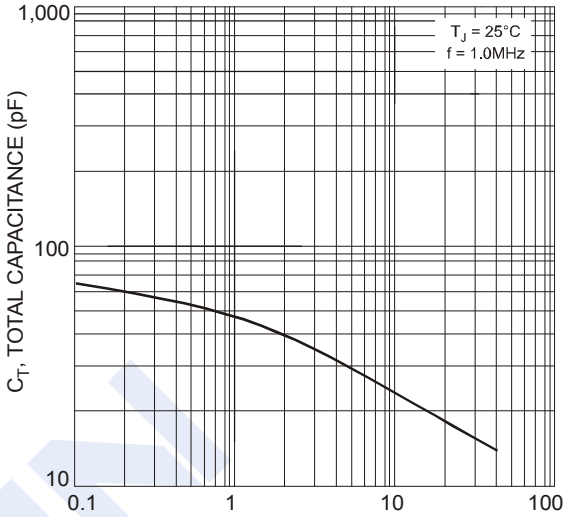


Fig. 2 Total Capacitance vs. Reverse Voltage

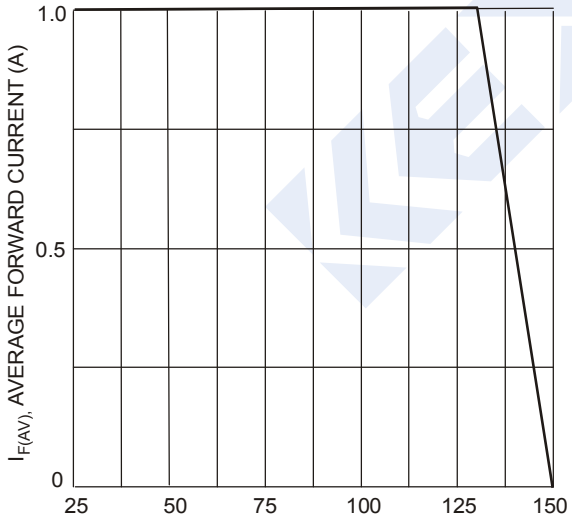


Fig. 3 Forward Current Derating Curve

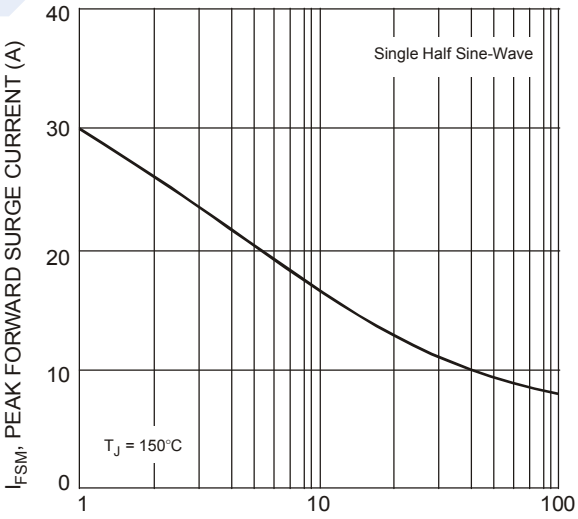


Fig. 4 Max Non-Repetitive Peak Forward Surge Current